Features

- Three high-side and three low-side drivers
- Outputs freely configurable as switch, half bridge or H-bridge
- Capable to switch all kinds of loads such as DC motors, bulbs, resistors, capacitors and inductors
- 0.6 A continuous current per switch
- Low-side: R_{DSon} < 1.5 Ω vs. total temperature range
- High-side: R_{DSon} < 2.0 Ω vs. total temperature range
- Very low quiescent current Is < 20 μA in standby mode
- Outputs short-circuit protected
- Overtemperature prewarning and protection
- Undervoltage and overvoltage protection
- Various diagnosis functions such as shorted output, open load, overtemperature and power supply fail
- Serial data interface
- Daisy chaining possible
- Loss of ground protection
- SSO20 package

Description

The T6817 is a fully protected driver interface designed in 0.8- μ m BCDMOS technology. It is used to control up to 6 different loads by a microcontroller in automotive and industrial applications.

Each of the 3 high-side and 3 low-side drivers is capable to drive currents up to 600 mA. The drivers are freely configurable and can be controlled separately from a standard serial data interface. Therefore, all kinds of loads such as bulbs, resistors, capacitors and inductors can be combined. The IC design especially supports the applications of H-bridges to drive DC motors.

Protection is guaranteed in terms of short-circuit conditions, overtemperature, underand overvoltage. Various diagnosis functions and a very low quiescent current in standby mode open a wide range of applications. Automotive qualification referring to conducted interferences, EMC protection and 2 kV ESD protection gives added value and enhanced quality for the exacting requirements of automotive applications. *wireLess & μc* Dual Triple DMOS Output Driver with

Serial Input Control

T6817

Ordering Information

Extended Type Number	Package	Remarks
T6817-TKS	SSO20	Power package, tube
T6817-TKQ	SSO20	Power package, taped and reeled







Block Diagram

Figure 1.



Pin Configuration

1

Figure 2. Pinning SSO20

	1 (20	ם מאם
	\cup	20	
DI 🗆	2	19	□ vcc
CS 🗆	3	18	
CLK 🗆	4	17	LS1
INH 🗆	5	16	HS1
VS 🗆	6	15	LS2
VS 🗆	7	14	HS2
LS3 🗆	8	13	🗆 GND
n.c. 🗆	9	12	□ HS3
GND 🗆	10	11	🗅 GND

Pin Description

Pin	Symbol	Function
1	GND	Ground; reference potential; internal connection to Pin 10, 11, 13 and 20; cooling tab
2	DI	Serial data input; 5-V CMOS logic level input with internal pull-down; receives serial data from the control device, DI expects a 16-bit control word with LSB being transferred first
3	CS	Chip–select input; 5-V CMOS logic level input with internal pull-up; low = serial communication is enabled, high = disabled
4	CLK	Serial clock input; 5-V CMOS logic level input with internal pull down; controls serial data input interface and internal shift register (fmax = 2 MHz)
5	INH	Inhibit input; 5-V logic input with internal pull–down; low = standby, high = normal operating
6, 7	VS	Power supply output stages HS1, HS2 and HS3
8	LS3	Low-side driver output 3; power-MOS open drain with internal reverse diode: overvoltage protection by active zenering; short-circuit protection; diagnosis for short and open load
9	n.c.	Not connected
10	GND	Ground, see Pin 1
11	GND	Ground, see Pin 1
12	HS3	High-side driver output 3; power-MOS open drain with internal reverse diode: overvoltage protection by active zenering; short-circuit protection; diagnosis for short and open load
13	GND	Ground, see Pin 1
14	HS2	High-side driver output 2; see Pin 12
15	LS2	Low-side driver output 2; see Pin 8
16	HS1	High-side driver output 1; see Pin 12
17	LS1	Low-side driver output 1; see Pin 8
18	DO	Serial data output; 5-V CMOS logic level tristate output for output (status) register data; sends 16-bit status information to the mC (LSB is transferred first); output will remain tristated unless device is selected by CS = low, therefore, several ICs can operate on one data output line only.
19	VCC	Logic supply voltage (5 V)
20	GND	Ground, see Pin 1





Functional Description

Serial Interface

Data transfer starts with the falling edge of the CS signal. Data must appear at DI synchronized to CLK and are accepted on the falling edge of the CLK signal. LSB (bit 0, SRR) has to be transferred first. Execution of new input data is enabled on the rising edge of the CS signal. When CS is high, Pin DO is in tristate condition. This output is enabled on the falling edge of CS. Output data will change their state with the rising edge of CLK and stay stable until the next rising edge of CLK appears. LSB (bit 0, TP) is transferred first.

Figure 3. Data transfer input data protocol



Input Data Protocol

Bit	Input Register	Function
0	SRR	Status register reset (high = reset; the bits PSF, SCD and overtemperature shutdown in the output data register are set to low)
1	LS1	Controls output LS1 (high = switch output LS1 on)
2	HS1	Controls output HS1 (high = switch output HS1 on)
3	LS2	See LS1
4	HS2	See HS1
5	LS3	See LS1
6	HS3	See HS1
7	n.u.	Not used
8	n.u.	Not used
9	n.u.	Not used
10	n.u.	Not used
11	n.u.	Not used
12	n.u.	Not used
13	OLD	Open load detection (low = on)
14	SCT	Programmable time delay for short circuit and overvoltage shutdown (short circuit shutdown delay high / low = 100 ms / 12.5 ms, overvoltage shutdown delay high / low = 14 ms / 3.5 ms
15	SI	Software inhibit; low = standby, high = normal operation (data transfer is not affected by standby function because the digital part is still powered)

4 (16) **T6817**

Output Data Protocol

Bit	Output (Status) Register	Function
0	TP	Temperature prewarning: high = warning (overtemperature shut- down see remark below)
1	Status LS1	Normal operation: high = output is on, low = output is off Open-load detection: high = open load, low = no open load (correct load condition is detected if the corresponding output is switched off)
2	Status HS1	Normal operation: high = output is on, low = output is off Open-load detection: high = open load, low = no open load (correct load condition is detected if the corresponding output is switched off)
3	Status LS2	Description see LS1
4	Status HS2	Description see HS1
5	Status LS3	Description see LS1
6	Status HS3	Description see HS1
7	n.u.	Not used
8	n.u.	Not used
9	n.u.	Not used
10	n.u.	Not used
11	n.u.	Not used
12	n.u.	Not used
13	SCD	Short circuit detected: set high, when at least one output is switched off by a short circuit condition
14	INH	Inhibit: this bit is controlled by software (bit SI in input register) and hardware inhibit (Pin 17). High = standby, low = normal operation
15	PSF	Power supply fail: undervoltage at Pin VS detected

Note: Bit 0 to 15 = high: overtemperature shutdown

After	power-on	reset,	the in	put reg	ister ha	s the	following	status
		,						

Bit 15 (SI)	Bit 14 (SCT)	Bit 13 (OLD)	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6 (HS3)	Bit 5 (LS3)	Bit 4 (HS2)	Bit 3 (LS2)	Bit 2 (HS1)	Bit 1 (LS1)	Bit 0 (SRR)
Н	Н	н	n.u.	n.u.	n.u.	n.u.	n.u.	n.u.	L	L	L	L	L	L	L

Power-Supply Fail

In case of undervoltage at Pin VS, an internal timer is started. When the undervoltage delay time (t_{dUV}) programmed by the SCT bit is reached, the power supply fail bit (PSF) in the output register is set and all outputs are disabled. When normal voltage is present again, the outputs are enabled immediately. The PSF bit remains high until it is reset by the SRR bit in the input register.



		ł
		R
WIRE	LESS & µC	

Open-Load Detection	If the open-load detection bit (OLD) is set to low, a pull-up current for each high-side switch and a pull-down current for each low-side switch is turned on (open-load detection current I_{HS1-3} , I_{LS1-3}). If V_{VS} - V_{HS1-3} or V_{LS1-3} is lower than the open-load detection threshold (open-load condition), the corresponding bit of the output in the output register is set to high. Switching on an output stage with OLD bit set to low disables the open-load function for this output. If bit SI is set to low, the open-load function is also switched off.
Overtemperature Protection	If the junction temperature exceeds the thermal prewarning threshold, $T_{jPW set}$, the temperature prewarning bit (TP) in the output register is set. When the temperature falls below the thermal prewarning threshold, $T_{jPW reset}$, the bit TP is reset. The TP bit can be read without transferring a complete 16-bit data word: with CS = high to low, the state of TP appears at Pin DO. After the μ C has read this information, CS is set high and the data transfer is interrupted without affecting the state of the input and output registers.
	If the junction temperature exceeds the thermal shutdown threshold, $T_{j \text{ switch off}}$, the outputs are disabled and all bits in the output register are set high. The outputs can be enabled again when the temperature falls below the thermal shutdown threshold, $T_{j \text{ switch}}$ on, and when a high has been written to the SRR bit in the input register. Thermal prewarning and shutdown threshold have hysteresis.
Short-Circuit Protection	The output currents are limited by a current regulator. Current limitation takes place when the overcurrent limitation and shutdown threshold (I_{HS1-3} , I_{LS1-3}) are reached. Simultaneously, an internal timer is started. The shorted output is disabled when during a permanent short the delay time (t_{dSd}) programmed by the short–circuit timer bit (SCT) is reached. Additionally, the short-circuit detection bit (SCD) is set. If the temperature prewarning bit TP in the output register is set during a short, the shorted output is disabled immediately and SCD bit is set. By writing a high to the SRR bit in the input register, the SCD bit is reset and the disabled outputs are enabled.
Inhibit	There are two ways to inhibit the T6817:
	 Set bit SI in the input register to zero Switch Pin 5 (INH) to 0 V

In both cases, all output stages are turned off but the serial interface stays active. The output stages can be activated again by bit SI = 1 or by Pin 5 (INH) switched back to 5 V

Absolute Maximum Ratings

All values refer to GND pins

Parameter		Symbol	Value	Unit
Supply voltage	Pins 6, 7	V _{VS}	- 0.3 to 40	V
Supply voltage tt0.5 s; I _S u-2 A	Pins 6, 7	V _{VS}	- 1	V
Supply voltage difference $ V_{S_Pin6} - V_{S_Pin7} $		ΔV_{VS}	150	mV
Supply current	Pins 6, 7	I _{VS}	1.4	А
Supply current t < 200 ms	Pins 6, 7	I _{VS}	2.6	А
Logic supply voltage	Pin 19	V _{VCC}	-0.3 to 7	V
Input voltage	Pin 5	V _{INH}	-0.3 to 17	V
Logic input voltage	Pins 2 to 4	$V_{DI,}V_{CLK,}V_{CS}$	-0.3 to V _{VCC} + 0.3	V
Logic output voltage	Pin 18	V _{DO}	-0.3 to V _{VCC} + 0.3	V
Input current	Pins 5, 2 to 4	I _{INH,} I _{DI,} I _{CLK,} I _{CS}	-10 to +10	mA
Output current	Pib 18	I _{DO}	-10 to +10	mA
Output current	Pins 1 to 4, 11 to 16, 27 and 28	I _{LS1 to} I _{LS3} I _{HS1 to} I _{HS3}	Internal limited, see output specification	
Reverse conducting current (t _{Pulse} = 150 ms)	Pins 12, 14, 16 towards 6, 7	I _{HS1 to} I _{HS3}	17	А
Junction temperature range		Tj	-40 to 150	°C
Storage temperature range		T _{STG}	-55 to 150	°C

Thermal Resistance

All values refer to GND pins

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Junction - pin	Measured to GND Pins 1, 10, 11, 13 and 20	R _{thJP}			25	K/W
Junction ambient		R _{thJA}			65	K/W

Operating Range

All values refer to GND pins

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	Pins 6, 7	V _{VS}	V _{UV} ¹⁾		40 ²⁾	V
Logic supply voltage	Pin 19	V _{VCC}	4.5	5	5.5	V
Logic input voltage	Pin 2 to 4 and 5	$\begin{array}{c} V_{\text{INH,}} V_{\text{DI,}} \\ V_{\text{CLK,}} V_{\text{CS}} \end{array}$	-0.3		V _{VCC}	V
Serial interface clock frequency	Pin 4	f _{CLK}			2	MHz
Junction temperature range		T _j	-40		150	°C

Notes: 1. Threshold for undervoltage detection

2. Outputs disabled for $V_{VS} > V_{OV}$ (threshold for overvoltage detection)





Noise and Surge Immunity

Parameter	Test Conditions	Value
Conducted interferences	ISO 7637–1	Level 4 ¹⁾
Interference Suppression	VDE 0879 Part 2	Level 5
ESD (Human Body Model)	MIL-STM 5.1 – 1998	2 kV
ESD (Machine Model)	JEDEC EIA / JESD 22 – A115-A	150 V

Note: 1. Test pulse 5: V_{Smax} = 40 V

Electrical Characteristics

7.5 V < V_{VS} < V_{OV}; 4.5 V < V_{VCC} < 5.5 V; INH = High; -40°C < T_j < 150°C; unless otherwise specified, all values refer to GND pins.

No.	Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit	Type*
1	Current Consumption								
1.1	Quiescent current (VS)	V_{VS} < 16 V, INH or bit SI = lo	6, 7	I _{VS}			40	μA	А
1.2	Quiescent current (VCC)	4.5 V $<$ V $_{\rm VCC}$ $<$ 5.5 V, INH or bit SI = low	19	I _{vcc}			20	μA	A
1.3	Supply current (VS)	V _{VS} < 16 V normal operating, all output stages off,	6, 7	I _{VS}		0.8	1.2	mA	A
1.4	Supply current (VS)	V _{VS} < 16 V normal operating, all output stages on, no load	6, 7	I _{VS}			10	mA	А
1.5	Supply current (VCC)	4.5 V $<$ V _{VCC} $<$ 5.5 V, normal operating Pin	19	I _{vcc}			150	μA	A
2	Internal Oscillator Fre	quency							
2.1	Frequency (timebase for delay timers)			f _{osc}	19		45	kHz	A
3	Over- and Undervoltage	ge Detection, Power-On	Reset						
3.1	Power-on reset threshold		19	V _{VCC}	3.4	3.9	4.4	V	A
3.2	Power-on reset delay time	After switching on V _{VCC}	19	t _{dPor}	30	95	160	μs	A
3.3	Undervoltage detection threshold		6, 7	V _{UV}	5.5		7.0	V	A
3.4	Undervoltage detection hysteresis		6, 7	ΔV_{UV}		0.4		V	A
3.6	Undervoltage detection delay		6, 7	t _{dUV}	7		21	ms	A
3.7	Overvoltage detection threshold		6, 7	V _{OV}	18.0		22.5	V	A
38	Overvoltage detection hysteresis		6, 7	ΔV_{OV}		1		V	A
*) Type	means: A =100% tested,	B = 100% correlation tes	sted, $C = 0$	Characterized	on sample	s, D = Desi	gn parame	ter	

Electrical Characteristics

7.5 V < V_{VS} < V_{OV}; 4.5 V < V_{VCC} < 5.5 V; INH = High; -40°C < T_j < 150°C; unless otherwise specified, all values refer to GND pins.

No.	Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit	Type*
3.9	Undervoltage detection delay	Input register bit 14 (SCT) = high bit 14 (SCT) = low		t _{dOV} t _{dOV}	7 1.75		21 5.25	ms ms	A
4	Thermal Prewarning	and Shutdown		Į	Į	Į	Į	4	4
4.1	Thermal prewarning			T _{iPWset}	125	145	165	°C	А
4.2	Thermal prewarning			T _{jPWreset}	105	125	145	°C	А
4.3	Thermal prewarning hysteresis			ΔT_{jPW}	3	20		к	А
4.4	Thermal shutdown			T _{j switch off}	150	170	190	°C	А
4.5	Thermal shutdown			T _{j switch on}	130	150	170	°C	A
4.6	Thermal shutdown hysteresis			$\Delta T_{j \text{ switch off}}$	3	20		к	А
4.7	Ratio thermal shutdown / thermal prewarning			T _{j switch off/} T _{jPW set}	1.05	1.17			А
4.8	Ratio thermal shutdown / thermal prewarning			T _{j switch on/} T _j PW reset	1.05	1.2			А
5	Output Specification	(LS1 - LS6, HS1 - HS6)	7.5 V < V	$VS < V_{OV}$					•
5.1	On resistance	I _{Out} = 600 mA	8, 15, 17	R _{DS OnL}			1.5	Ω	A
5.2	On resistance	I _{Out} = -600 mA	12, 14, 16	R _{DS OnH}			2.0	Ω	A
5.3	Output clamping voltage	I _{LS1-3} = 50 mA	8, 15, 17	V _{LS1-3}	40		60	V	A
5.4	Output leakage current	V _{LS1-3} = 40 V all output stages off	8, 15, 17	I _{LS1–3}			10	μΑ	A
5.5	Output leakage current	V _{HS1-3} = 0 V all output stages off	2, 3, 12, 13, 15, 28	I _{HS1-3}	-10			μA	A
5.7	Inductive shutdown energy		8, 12, 14 to 17	W _{outx}			15	mJ	D
5.8	Output voltage edge steepness		8, 12, 14 to 17	dV _{LS1–3} /dt dV _{HS1–3} /dt	50	200	400	mV/μs	A
5.9	Overcurrent limitation and shutdown threshold		8, 15, 17	I _{LS1–3}	650	950	1250	mA	A
5.10	Overcurrent limitation and shutdown threshold		12, 14, 16	I _{HS1–3}	-1250	-950	-650	mA	A





Electrical Characteristics

7.5 V < V_{VS} < V_{OV}; 4.5 V < V_{VCC} < 5.5 V; INH = High; -40°C < T_j < 150°C; unless otherwise specified, all values refer to GND pins.

No.	Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit	Type*	
5.11	Overcurrent shutdown delay time	Input register bit 14 (SCT) = high bit 14 (SCT) = low		t _{dSd} t _{dSd}	8 1.0	12 1.5	16 2.0	ms ms	A A	
5.12	Open load detection current	Input register bit 13 (OLD) =low, output off	8, 15, 17	I _{LS1-3}	60		200	μA	A	
5.13	Open load detection current	Input register bit 13 (OLD) =low, output off	12, 14, 16	I _{HS1–3}	-150		-30	μA	A	
5.14	Open load detection current ratio		8, 15, 17	I _{LS1–3 /} I _{HS1–3}	1.2				А	
5.15	Open load detection threshold	Input register bit 13 (OLD) =low, output off	12, 14, 16	V _{LS1-3}	0.6		4	V	А	
5.16	Open load detection threshold	Input register bit 13 (OLD) =low, output off	2, 3, 12, 13 15, 28	V _{VS-} V _{HS1-3}	0.6		4	V	A	
5.17	Output switch on delay ¹⁾	$R_{Load} = 1 \ k\Omega$		t _{don}			0.5	ms	А	
5.18	Output switch off delay ¹⁾	$R_{Load} = 1 \ k\Omega$		t _{doff}			1	ms	А	
6	Inhibit Input	•						*		
6.1	Input voltage low level threshold		5	V _{IL}	0.3- V _{VCC}			V	A	
6.2	Input voltage high level threshold		5	V _{IH}			0.7- V _{VCC}	V	A	
6.3	Hysteresis of input voltage		5	ΔV_{I}	100		700	mV	A	
6.4	Pull-down current	$V_{INH} = V_{VCC}$	5	I _{PD}	10		80	μA	А	
7	Serial Interface - Logi	c Inputs DI, CLK, CS								
7.1	Input voltage low- level threshold		2-4	V _{IL}	0.3- V _{VCC}			V	A	
7.2	Input voltage high- level threshold		2-4	V _{IH}			0.7- V _{VCC}	V	A	
7.3	Hysteresis of input voltage		2-4	ΔV_{I}	50		500	mV	A	
7.4	Pull-down current Pin DI, CLK	$V_{DI}, V_{CLK} = V_{VCC}$	2, 4	I _{PDSI}	2		50	μA	А	
7.5	Pull-up current Pin CS	V _{CS} = 0 V	3	I _{PUSI}	-50		-2	μA	А	
Note:	1. Delay time between	rising edge of CS after d	ata transr	nission and sv	vitch on ou	tput stages	to 90% of	final level		
*) Type	*) Type means: A =100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter									

Electrical Characteristics

7.5 V < V_{VS} < V_{OV}; 4.5 V < V_{VCC} < 5.5 V; INH = High; -40°C < T_j < 150°C; unless otherwise specified, all values refer to GND pins.

No.	Parameters	Test Conditions	Pin	Symbol	Min.	Тур.	Max.	Unit	Type*		
8	Serial Interface - Logic Output DO										
8.1	Output voltage low level	I _{OL} = 3 mA	18	V _{DOL}			0.5	V	А		
8.2	Output voltage high level	I _{OL} = -2 mA	18	V _{DOH}	V _{VCC} - 1 V			V	А		
8.3	Leakage current (tristate)	$\begin{array}{c} V_{\text{CS}} = V_{\text{VCC},} \\ 0 \ V < V_{\text{DO}} < V_{\text{VCC}} \end{array}$	18	I _{DO}	-10		10	μA	А		
*) Type	*) Type means: A =100% tested, B = 100% correlation tested, C = Characterized on samples, D = Design parameter										

Serial Interface – Timing

Parameters	Test Conditions	Timing Chart No.	Symbol	Min.	Тур.	Max.	Unit
DO enable after CS falling edge	C _{DO} = 100 pF	1	t _{ENDO}			200	ns
DO disable after CS rising edge	C _{DO} = 100 pF	2	t _{DISDO}			200	ns
DO fall time	C _{DO} = 100 pF	-	t _{DOf}			100	ns
DO rise time	C _{DO} = 100 pF	-	t _{DOr}			100	ns
DO valid time	C _{DO} = 100 pF	10	t _{DOVal}			200	ns
CS setup time		4	t _{CSSethl}	225			ns
CS setup time		8	t _{CSSetlh}	225			ns
CS high time	Input register Bit 14 (SCT) = high	9	t _{CSh}	140			ms
CS high time	Input register Bit 14 (SCT) = low	9	t _{CSh}	17.5			ms
CLK high time		5	t _{CLKh}	225			ns
CLK low time		6	t _{CLKI}	225			ns
CLK period time		-	t _{CLKp}	500			ns
CLK setup time		7	t _{CLKSethl}	225			ns
CLK setup time		3	t _{CLKSetlh}	225			ns
DI setup time		11	t _{DIset}	40			ns
DI hold time		12	t _{DIHold}	40			ns





Figure 4. Serial interface timing with chart numbers



Inputs DI, CLK, CS: High level = 0.7 x V_{CC}, low level = 0.3 x V_{CC} Output DO: High level = 0.8 x V_{CC}, low level = 0.2 x V_{CC}

Application Circuit

Figure 5.



Application Notes

It is strongly recommended to connect the blocking capacitors at V_{CC} and V_S as close as possible to the power supply and GND pins.

Recommended value for capacitors at V_S:

electrolythic capacitor C > 22 μ F in parallel with a ceramic capacitor C = 100 nF. Value for electrolytic capacitor depends on external loads, conducted interferences and reverse conducting current I_{HSX} (see: Absolut Maximum Ratings).

Recommended value for capacitors at V_{CC}: electrolythic capacitor C > 10 μ F in parallel with a ceramic capacitor C = 100 nF.

To reduce thermal resistance it is recommended to place cooling areas on the PCB as close as possible to GND pins.





Package Information

Figure 6.



Ozone Depleting Substances Policy Statement

It is the policy of Atmel Germany GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Atmel Germany GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Atmel Germany GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.





Atmel Wireless & Microcontrollers Sales Offices

France

3, Avenue du Centre 78054 St.-Quentin-en-Yvelines Cedex Tel: +33 1 30 60 70 00 Fax: +33 1 30 60 71 11

Germany

Erfurter Strasse 31 85386 Eching Tel: +49 89 319 70 0 Fax: +49 89 319 46 21

Kruppstrasse 6 45128 Essen Tel: +49 201 247 30 0 Fax: +49 201 247 30 47

Theresienstrasse 2 74072 Heilbronn Tel: +49 7131 67 36 36 Fax: +49 7131 67 31 63

Italy

Via Grosio, 10/8 20151 Milano Tel: +39 02 38 03 71 Fax: +39 02 38 03 72 34

Spain

Principe de Vergara, 112 28002 Madrid Tel: +34 91 564 51 81 Fax: +34 91 562 75 14

Sweden

Kavallerivaegen 24, Rissne 17402 Sundbyberg Tel: +46 8 587 48 800 Fax: +46 8 587 48 850

United Kingdom

Easthampstead Road Bracknell Berkshire RG12 1LX Tel: +44 1344 707 300 Fax: +44 1344 427 371

USA Western

2325 Orchard Parkway San Jose, California 95131 Tel: +1 408 441 0311 Fax: +1 408 436 4200

USA Eastern

1465 Route 31, Fifth floor Annandale New Jersey 08801 Tel: +1 908 848 5208 Fax: +1 908 848 5232

Hong Kong

Room #1219, Chinachem Golden Plaza 77 Mody Road, Tsimhatsui East East Kowloon, Hong Kong Tel: +852 23 789 789 Fax: +852 23 755 733

Korea

25-4, Yoido-Dong, Suite 605, Singsong Bldg. Youngdeungpo-Ku 150-010 Seoul Tel: +822 785 1136 Fax: +822 785 1137

Rep. of Singapore

Keppel Building #03-00 25 Tampines Street 92, Singapore 528877 Tel: +65 260 8223 Fax: +65 787 9819

Taiwan, R.O.C.

8F-2, 266 Sec.1 Wen Hwa 2 Rd. Lin Kou Hsiang, 244 Taipei Hsien Tel: +886 2 2609 5581 Fax: +886 2 2600 2735

Japan

Tonetsushinkawa Bldg. 1-24-8 Shinkawa Chuo Ku Tokyo 104-0033 Tel: +81 3 3523 3551 Fax: +81 3 3523 7581

Web Site

http://www.atmel-wm.com

© Atmel Germany GmbH 2001.

Atmel Germany GmbH makes no warranty for the use of its products, other than those expressly contained in the Company's standard warranty which is detailed in Atmel Germany GmbH's Terms and Conditions. The Company assumes no responsibility for any errors which may appear in this document, reserves the right to change devices or specifications detailed herein at any time without notice, and does not make any commitment to update the information contained herein. No licenses to patents or other intellectual property of Atmel Germany GmbH are granted by the Company in connection with the sale of AtmelGermany GmbH products, expressly or by implication. Atmel Germany GmbH's products are not authorized for use as critical components in life support devices or systems.

Data sheets can also be retrieved fron the Internet: http://www.atmel-wm.com